

Features

- Split Gate Trench MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Applications

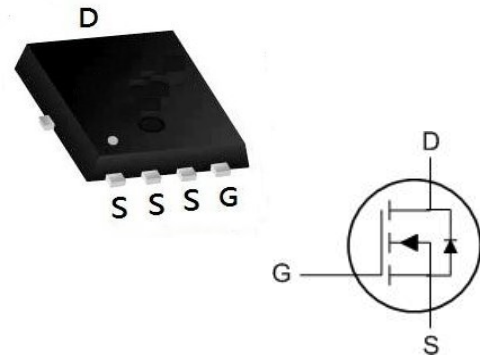
- DC-DC Converters
- Power management functions
- Synchronous-rectification applications

Product Summary



BVDSS	RDSON	ID
60V	1.1mΩ	200A

PDFN5060-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	200	A
$I_D@T_C=100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^{1,6}$	157	A
I_{DM}	Pulsed Drain Current ²	1000	A
EAS	Single Pulse Avalanche Energy ³	961	mJ
I_{AS}	Avalanche Current	---	A
$P_D@T_C=25^\circ\text{C}$	Total Power Dissipation ⁴	139	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-Ambient ¹	---	56	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	0.9	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	60	---	---	V
$\Delta BV_{DSS} / \Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	---	---	$V/^\circ\text{C}$
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V$, $I_D=1A$	---	1.1	1.4	m Ω
		$V_{GS}=4.5V$, $I_D=1A$	---	---	---	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	2.2	2.4	3.8	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	---	---	$\text{mV}/^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=60V$, $V_{GS}=0V$, $T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=60V$, $V_{GS}=0V$, $T_J=100^\circ\text{C}$	---	---	100	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=10V$, $I_D=14A$	---	209	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	1.7	---	Ω
Q_g	Total Gate Charge	$V_{DS}=30V$, $V_{GS}=10V$, $I_D=50A$	---	103	---	nC
Q_{gs}	Gate-Source Charge		---	38	---	
Q_{gd}	Gate-Drain Charge		---	13	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{GS}=10V$, $V_{DD}=30V$, $R_G=3\Omega$, $I_D=50A$	---	24.2	---	ns
T_r	Rise Time		---	58.2	---	
$T_{d(off)}$	Turn-Off Delay Time		---	62.5	---	
T_f	Fall Time		---	26.4	---	
C_{iss}	Input Capacitance	$V_{DS}=30V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	7156	---	pF
C_{oss}	Output Capacitance		---	2380	---	
C_{rss}	Reverse Transfer Capacitance		---	69	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	200	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V$, $I_S=7A$, $T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=7A$, $di/dt=100A/\mu s$, $T_J=25^\circ\text{C}$	---	73.4	---	nS
Q_{rr}	Reverse Recovery Charge		---	107.9	---	nC

Notes:

1. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}=150^\circ\text{C}$.
2. The test condition is $V_{DD}=45V$, $V_{GS}=10V$, $L=0.4\text{mH}$.
3. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper, The value in any given application depends on the user's specific board design.
4. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
5. This value is guaranteed by design hence it is not included in the production test.

Typical Performance Characteristics

Fig 1: Output Characteristics

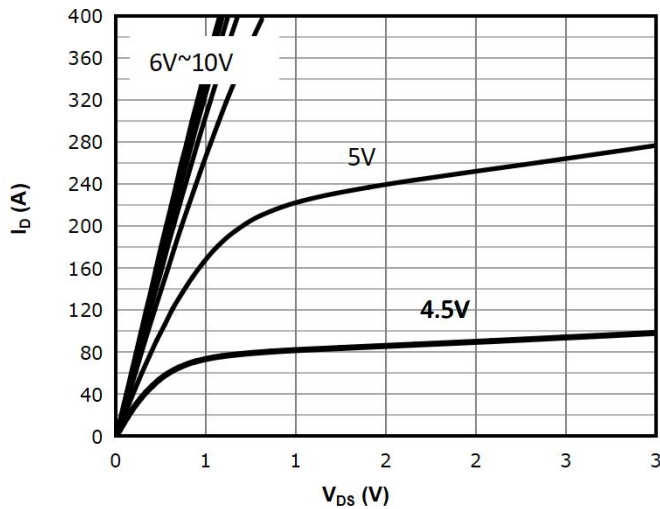


Fig 2: Transfer Characteristics

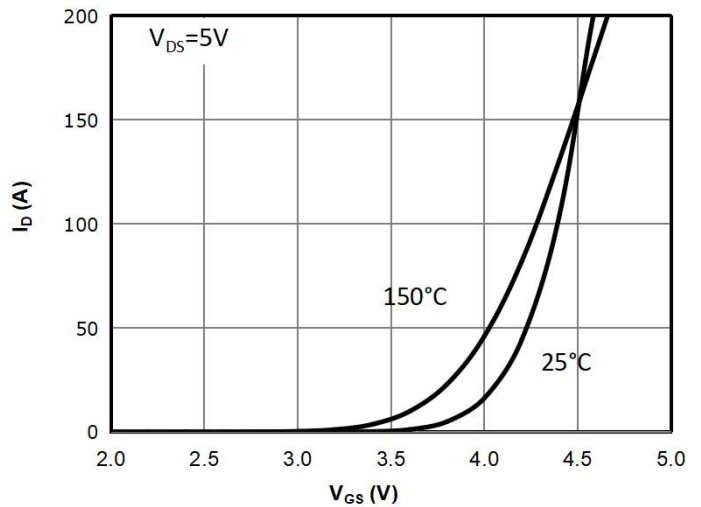


Fig 3: $R_{DS(on)}$ vs Drain Current and Gate Voltage

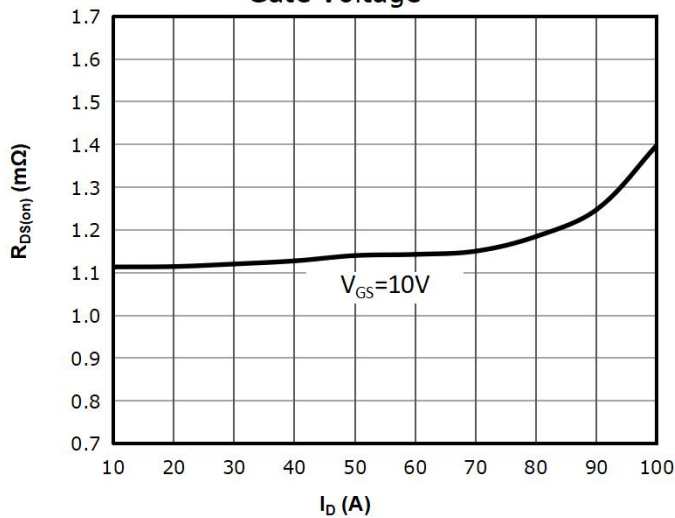


Fig 4: $R_{DS(on)}$ vs Gate Voltage

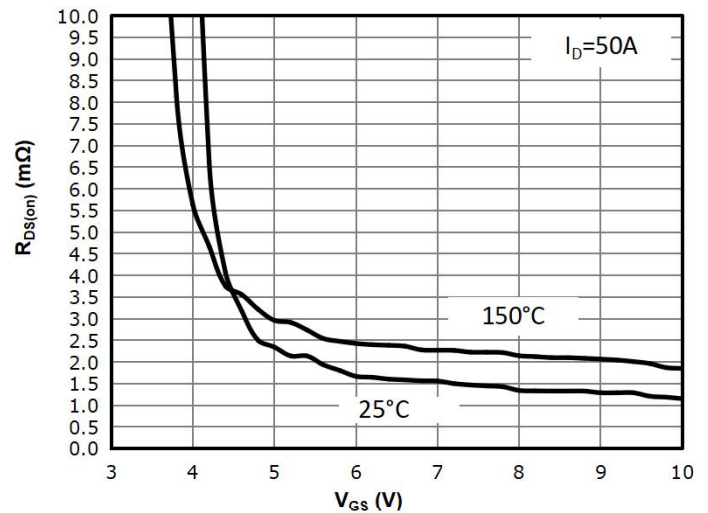


Fig 5: $R_{DS(on)}$ vs. Temperature

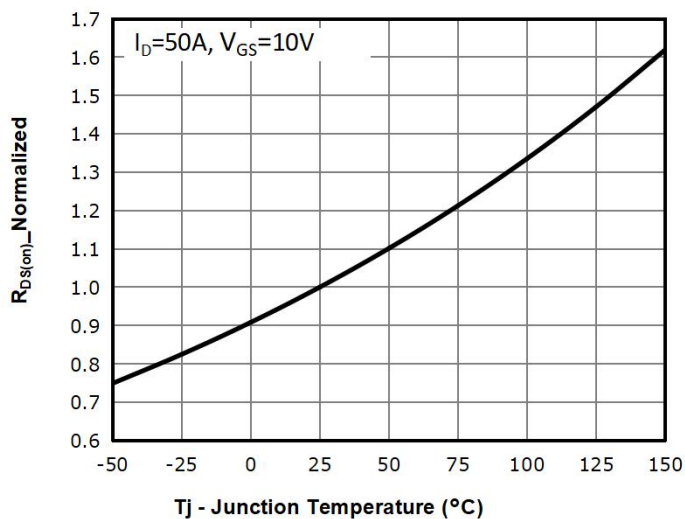


Fig 6: $V_{GS(th)}$ vs. Temperature

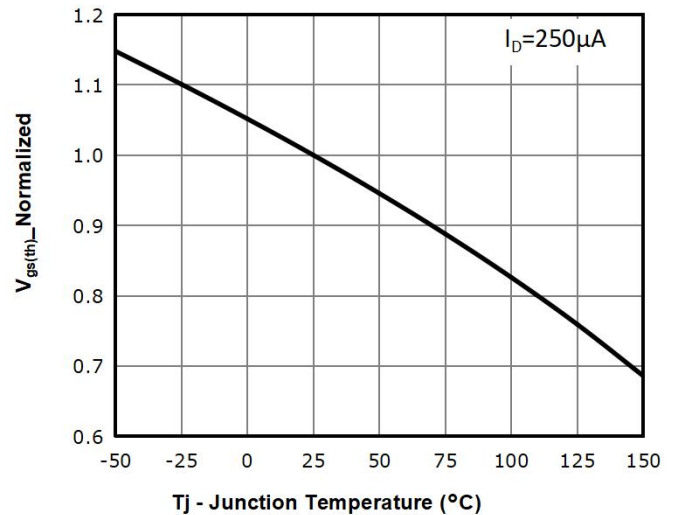


Fig 7: BVdss vs. Temperature

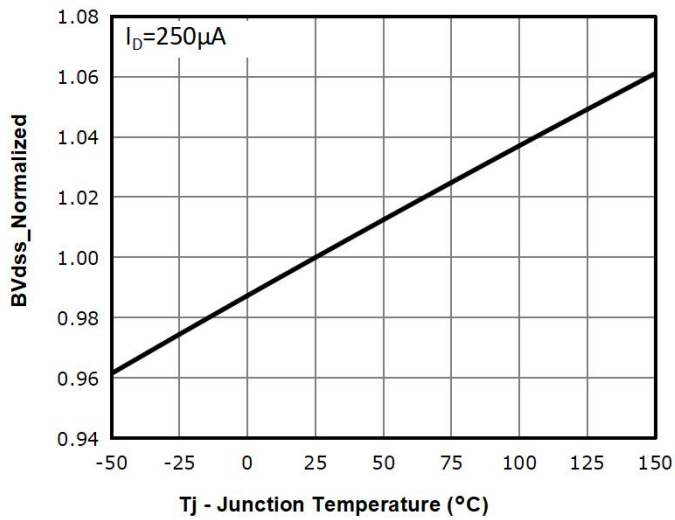


Fig 8: Capacitance Characteristics

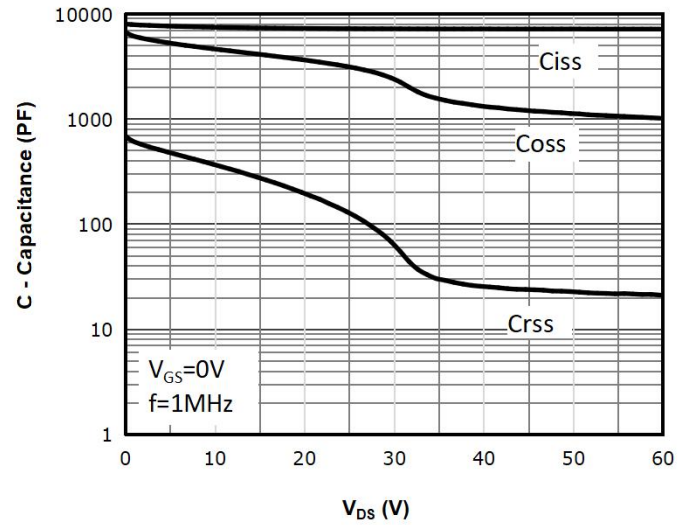


Fig 9: Gate Charge Characteristics

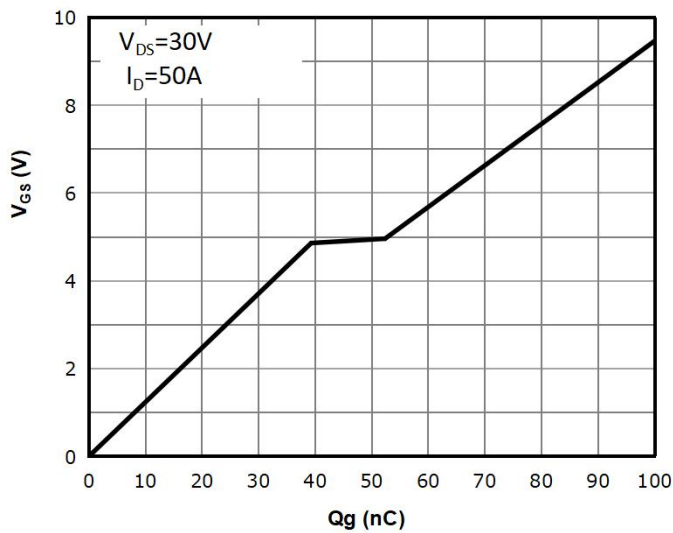


Fig 10: Body-diode Forward Characteristics

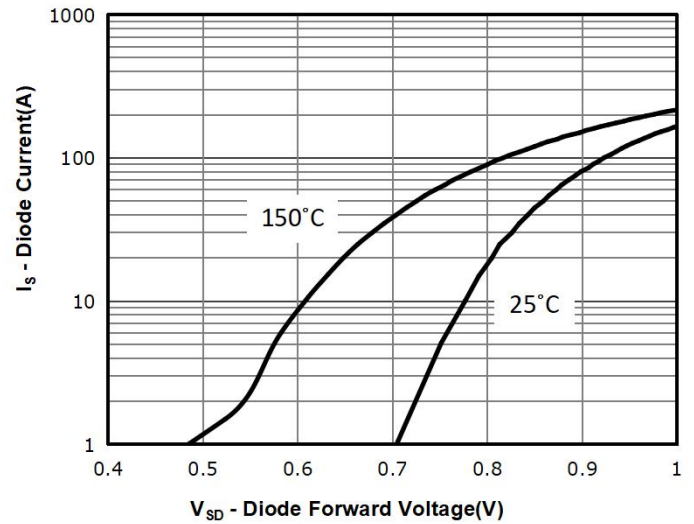


Fig 11: Power Dissipation

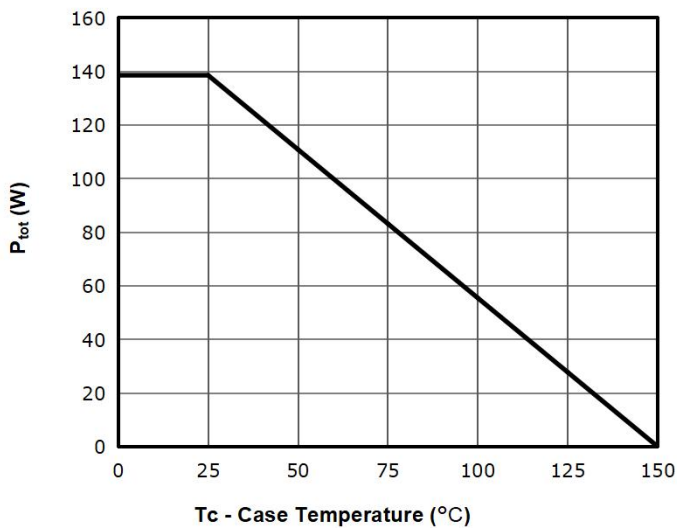


Fig 12: Drain Current Derating

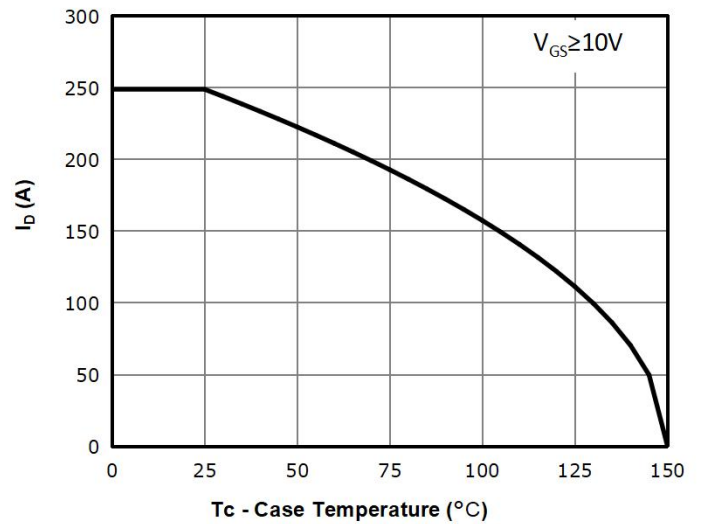


Fig 13: Safe Operating Area

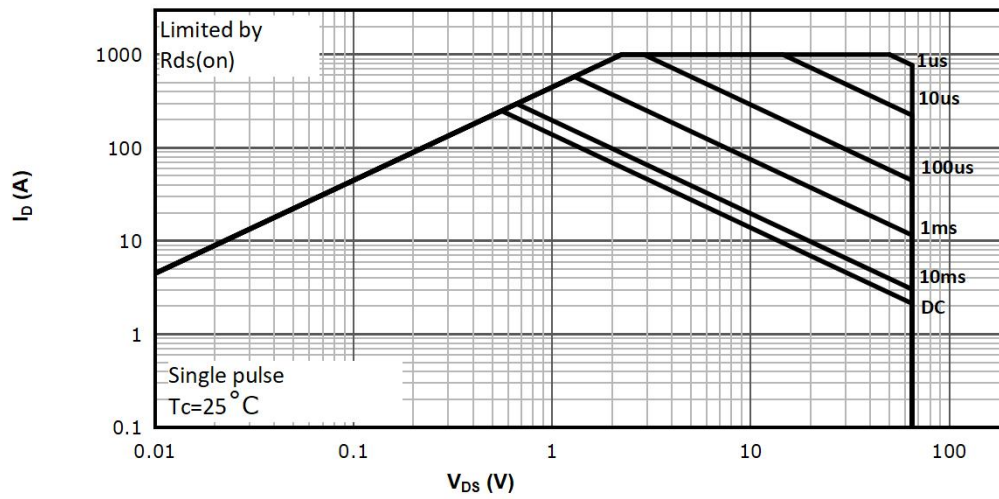
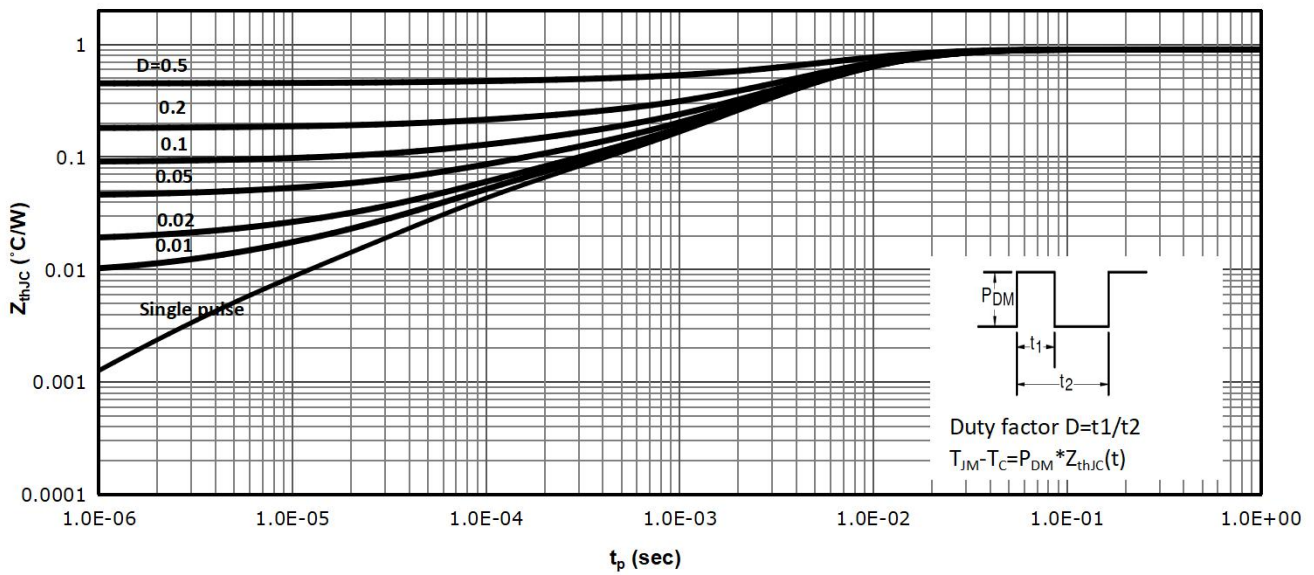
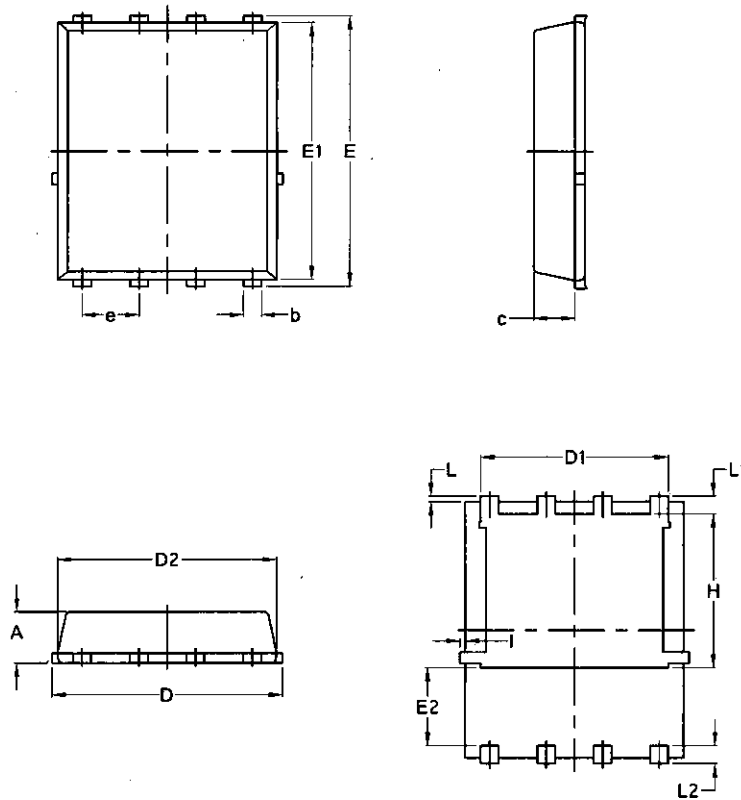


Fig 14: Max. Transient Thermal Impedance



Package Mechanical Data-PDFN5060-8L- Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070